Switching Transistor

PNP Silicon

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-40	Vdc
Collector - Base Voltage	V_{CBO}	-40	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2)	P_D	300	mW
T _A = 25°C Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

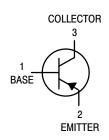
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318-08 STYLE 6

MARKING DIAGRAM



2T = Specific Device Code D = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (No (I _C = -1.0 mAdc, I _B = 0)	ote 3)	V _{(BR)CEO}	-40	_	Vdc	
Collector – Base Breakdown Voltage (I _C = -0.1 mAdc, I _E = 0)		V _{(BR)CBO}	-40	_	Vdc	
Emitter – Base Breakdown Voltage $(I_E = -0.1 \text{ mAdc}, I_C = 0)$	V _{(BR)EBO}	-5.0	_	Vdc		
Base Cutoff Current (V _{CE} = -35 Vdc, V _{EB} = -0.4 Vdc)	I _{BEV}	_	-0.1	μAdc		
Collector Cutoff Current (V _{CE} = -35 Vdc, V _{EB} = -0.4 Vdc)	I _{CEX}	-	-0.1	μAdc		
ON CHARACTERISTICS		•		•	-	
$\begin{array}{l} \text{DC Current Gain} \\ \text{(I}_{\text{C}} = -0.1 \text{ mAdc, V}_{\text{CE}} = -1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = -1.0 \text{ mAdc, V}_{\text{CE}} = -1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = -10 \text{ mAdc, V}_{\text{CE}} = -1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = -150 \text{ mAdc, V}_{\text{CE}} = -2.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = -500 \text{ mAdc, V}_{\text{CE}} = -2.0 \text{ Vdc)} \end{array} \\ (Note that the expectation of the $	•	h _{FE}	30 60 100 100 20	- - - 300 -	-	
Collector – Emitter Saturation Voltage (Note 3) ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)		V _{CE(sat)}	_ _	-0.4 -0.75	Vdc	
Base – Emitter Saturation Voltage (Note 3) (I_C = -150 mAdc, I_B = -15 mAdc) (I_C = -500 mAdc, I_B = -50 mAdc)	V _{BE(sat)}	-0.75 -	-0.95 -1.3	Vdc		
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain — Bandwidth Product (I _C = –20 mAdc, V _{CE} = –10 Vdc, f = 100	MHz)	f _T	200	-	MHz	
Collector–Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C _{cb}	-	8.5	pF	
Emitter–Base Capacitance $(V_{BE} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{eb}	-	30	pF	
Input Impedance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h _{ie}	1.5	15	kΩ	
Voltage Feedback Ratio $(I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h _{re}	0.1	8.0	X 10 ⁻⁴	
Small – Signal Current Gain $(I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h _{fe}	60	500	-	
Output Admittance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h _{oe}	1.0	100	μmhos	
SWITCHING CHARACTERISTICS		-				
Delay Time	$(V_{CC} = -30 \text{ Vdc}, V_{EB} = -2.0 \text{ Vdc},$	t _d	-	15	15 ns	
Rise Time	$I_C = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _r	-	20		
Storage Time Fall Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t _s	-	225 30	ns	
i dii i iiii C	,	t _f		30		

^{3.} Pulse Test: Pulse Width \leq 300 $\mu\text{s},$ Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT4403LT1	SOT-23 (TO-236)	3000 Tape & Reel
MMBT4403LT1G	SOT-23 (TO-236) (Pb-Free)	3000 Tape & Reel
MMBT4403LT3	SOT-23 (TO-236)	10,000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

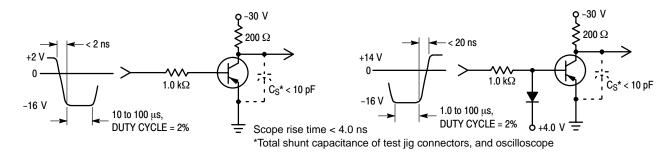


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

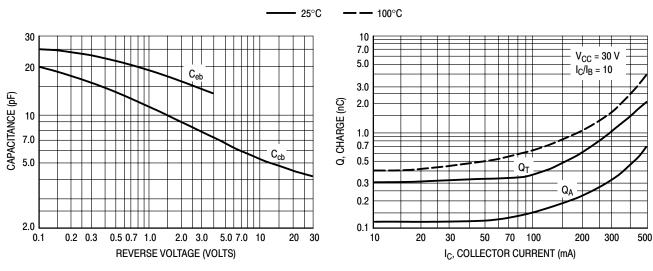


Figure 3. Capacitances

Figure 4. Charge Data

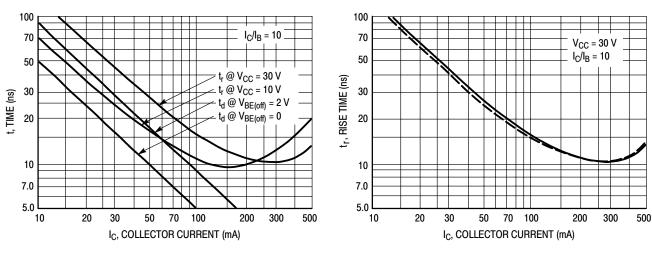


Figure 5. Turn-On Time

Figure 6. Rise Time

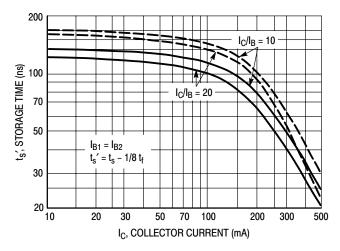


Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $V_{CE} = -10 \text{ Vdc}$, $T_A = 25^{\circ}\text{C}$; Bandwidth = 1.0 Hz

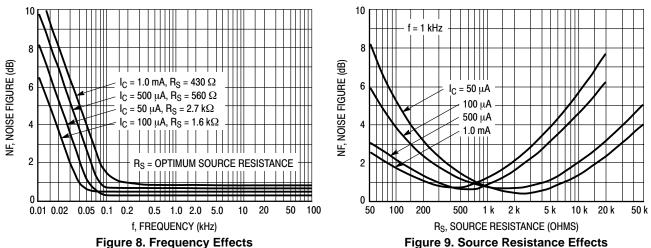


Figure 9. Source Resistance Effects

h PARAMETERS

 $V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

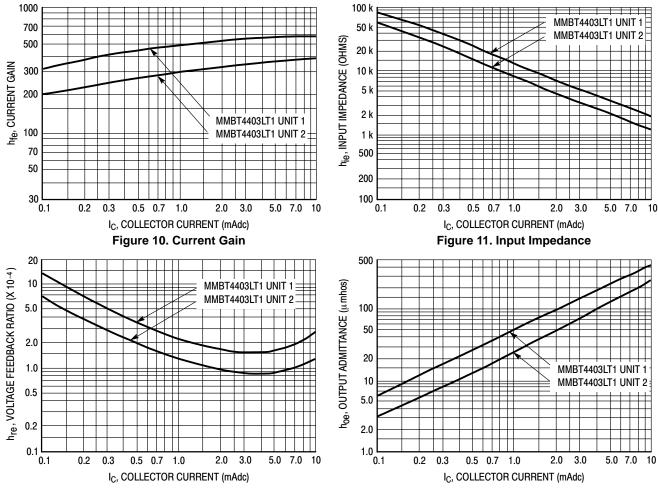


Figure 12. Voltage Feedback Ratio

Figure 13. Output Admittance

STATIC CHARACTERISTICS

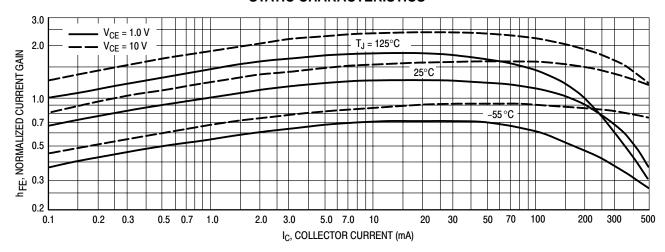


Figure 14. DC Current Gain

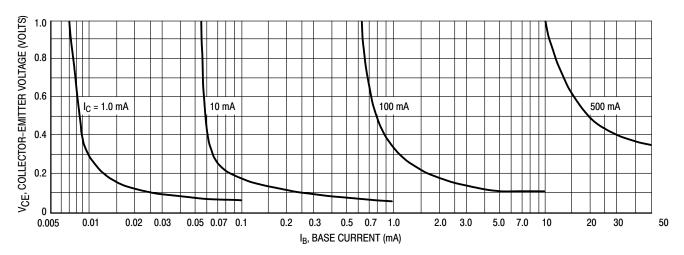


Figure 15. Collector Saturation Region

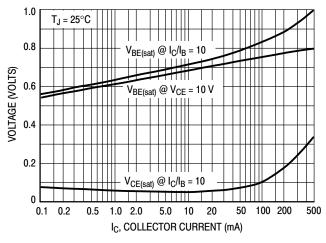


Figure 16. "On" Voltages

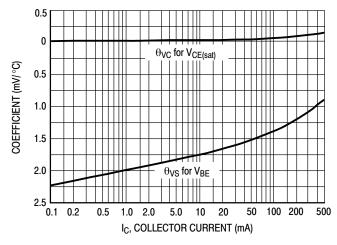
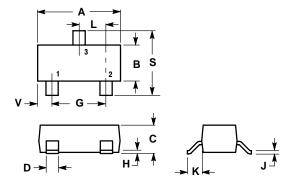


Figure 17. Temperature Coefficients

PACKAGE DIMENSIONS

CASE 318-08 SOT-23 (TO-236) **ISSUE AH**



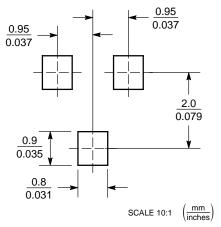
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATEDIAL
- MATERIAL.
 4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INCHES		INCHES MILLIMET		IETERS
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
C	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
٧	0.0177	0.0236	0.45	0.60	

- STYLE 6:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

SOLDERING FOOTPRINT*



SOT-23

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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